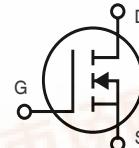




# RF POWER MOSFET

## N-CHANNEL ENHANCEMENT MODE

# ARF1501



250V 750W 40MHz

The ARF1501 is an RF power transistor designed for very high power scientific, commercial, medical and industrial RF power generator and amplifier applications up to 40 MHz.

- Specified 250 Volt, 27.12 MHz Characteristics:

Output Power = 750 Watts.

Gain = 17dB (Class C)

Efficiency > 75%

- High Performance Power RF Package.

- Very High Breakdown for Improved Ruggedness.

- Low Thermal Resistance.

- Nitride Passivated Die for Improved Reliability.

### MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	ARF1501	UNIT
$V_{DSS}$	Drain-Source Voltage	1000	Volts
$I_D$	Continuous Drain Current @ $T_C = 25^\circ\text{C}$	30	Amps
$V_{GS}$	Gate-Source Voltage	$\pm 30$	Volts
$P_D$	Total Device Dissipation @ $T_C = 25^\circ\text{C}$	1500	Watts
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 200	$^\circ\text{C}$
$T_L$	Lead Temperature: 0.063" from Case for 10 Sec.	300	

### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$BV_{DSS}$	Drain-Source Breakdown Voltage ( $V_{GS} = 0V, I_D = 250 \mu\text{A}$ )	1000			
$V_{DS(ON)}$	On State Drain Voltage ① ( $I_{D(ON)} = 15\text{A}, V_{GS} = 10\text{V}$ )		7.5	9	Volts
$I_{DSS}$	Zero Gate Voltage Drain Current ( $V_{DS} = 1000\text{V}, V_{GS} = 0\text{V}$ )			40	$\mu\text{A}$
	Zero Gate Voltage Drain Current ( $V_{DS} = 800\text{V}, V_{GS} = 0\text{V}, T_C = 125^\circ\text{C}$ )			1000	
$I_{GSS}$	Gate-Source Leakage Current ( $V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$ )			$\pm 400$	nA
$g_{fs}$	Forward Transconductance ( $V_{DS} = 25\text{V}, I_D = 15\text{A}$ )	5.5	7		mhos
$V_{isolation}$	RMS Voltage (60Hz Sinewave from terminals to mounting surface for 1 minute)	2500			Volts
$V_{GS(TH)}$	Gate Threshold Voltage ( $V_{DS} = V_{GS}, I_D = 50\text{mA}$ )	3		5	Volts

### THERMAL CHARACTERISTICS

Symbol	Characteristic (per package unless otherwise noted)	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.12	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Case to Sink (Use High Efficiency Thermal Joint Compound and Planar Heat Sink Surface.)		0.09		

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

## DYNAMIC CHARACTERISTICS

ARF1501

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 200V$ $f = 1\text{ MHz}$		5400	6500	pF
$C_{oss}$	Output Capacitance			300	400	
$C_{rss}$	Reverse Transfer Capacitance			125	160	
$t_{d(on)}$	Turn-on Delay Time	$V_{GS} = 15V$ $V_{DD} = 500V$ $I_D = I_{D[\text{Cont.}]} @ 25^\circ\text{C}$ $R_G = 1.6\Omega$		8		ns
$t_r$	Rise Time			5		
$t_{d(off)}$	Turn-off Delay Time			25		
$t_f$	Fall Time			13		

## FUNCTIONAL CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
$G_{PS}$	Common Source Amplifier Power Gain	$f = 27.12\text{ MHz}$ $V_{GS} = 0V$ $V_{DD} = 250V$ $P_{out} = 750W$	15	17		dB
$\eta$	Drain Efficiency		70	75		%
$\psi$	Electrical Ruggedness VSWR 10:1		No Degradation in Output Power			

① Pulse Test: Pulse width < 380  $\mu\text{S}$ , Duty Cycle < 2%.

APT Reserves the right to change, without notice, the specifications and information contained herein.

Per transistor section unless otherwise specified.

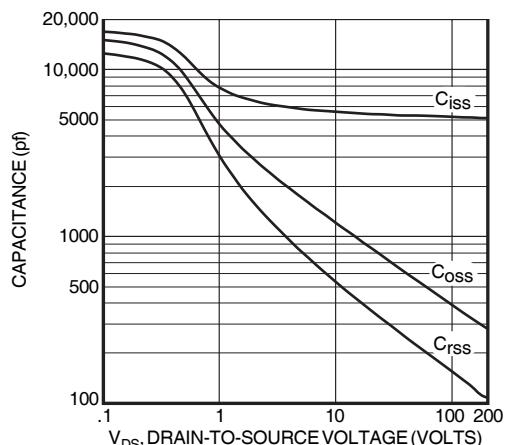
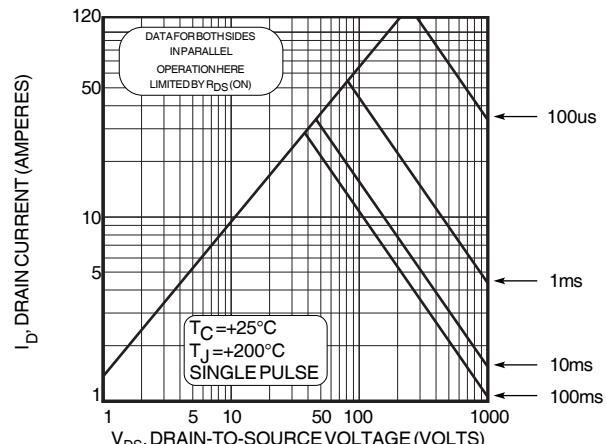
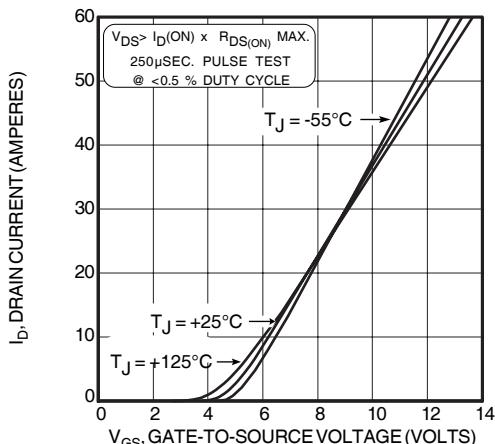


Figure 1, Typical Capacitance vs. Drain-to-Source Voltage



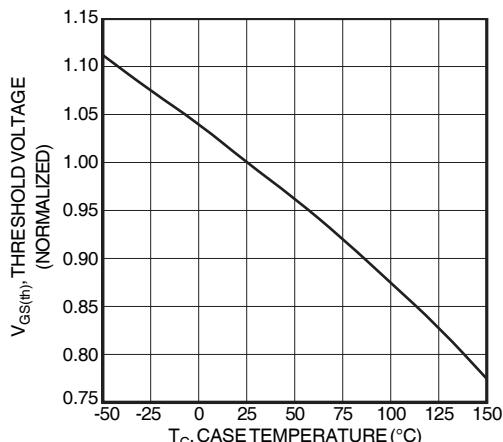


Figure 4, Typical Threshold Voltage vs Temperature

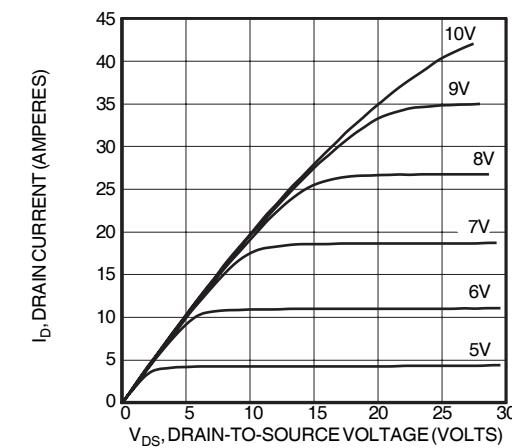


Figure 5, Typical Output Characteristics

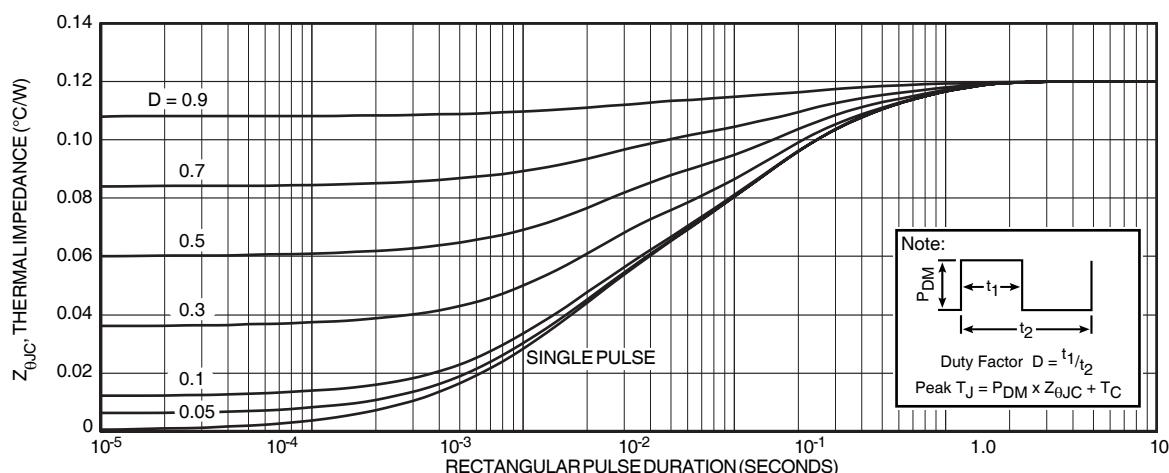


Figure 6, Maximum Effective Transient Thermal Impedance, Junction-to-Case vs. Pulse Duration

Table 1 - Typical Class AB Large Signal Impedance -- ARF1501

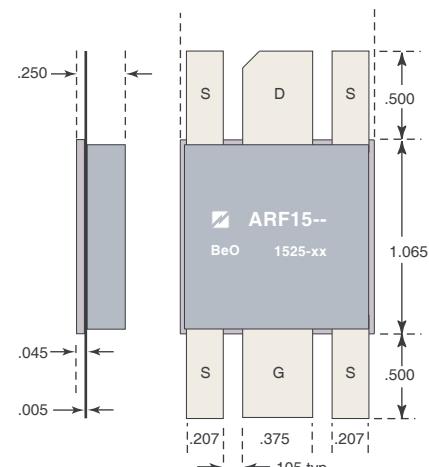
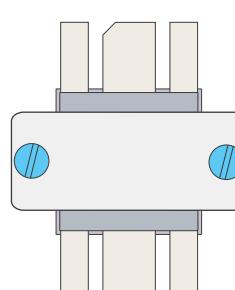
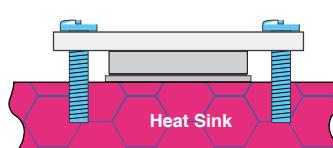
F (MHz)	Z <sub>in</sub> (Ω)	Z <sub>OL</sub> (Ω)
2.0	10.6 -j 12.2	31 -j 4.7
13.5	0.5 -j 2.7	15.6 -j 16
27	0.22 -j 0.8	6.2 -j 12.6
40	0.2 +j .12	3.1 -j 9.4

Z<sub>in</sub> - Gate shunted with 25Ω I<sub>DQ</sub> = 100mA  
Z<sub>OL</sub> - Conjugate of optimum load for 750 Watts output at V<sub>dd</sub> = 250V

#### Thermal Considerations and Package Mounting:

The rated 1500W power dissipation is only available when the package mounting surface is at 25°C and the junction temperature is 200°C. The thermal resistance between junctions and case mounting surface is 0.12°C/W. When installed, an additional thermal impedance of 0.1°C/W between the package base and the mounting surface is typical. Insure that the mounting surface is smooth and flat. Thermal joint compound must be used to reduce the effects of small surface irregularities. The heatsink should incorporate a copper heat spreader to obtain best results.

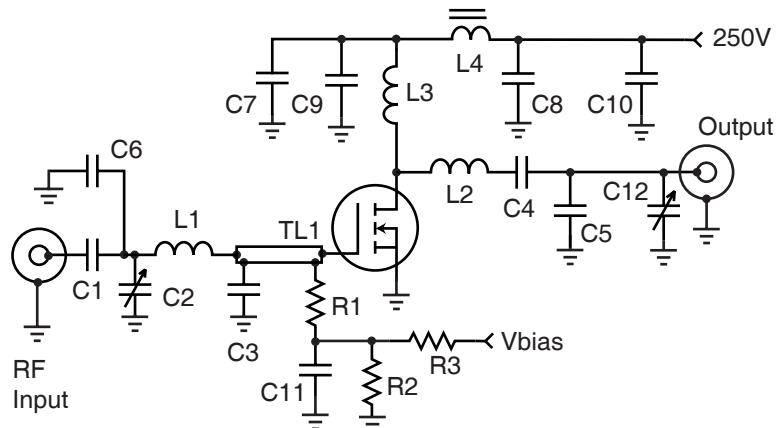
The package is designed to be clamped to a heatsink. A clamped joint maintains the required mounting pressure while allowing for thermal expansion of both the device and the heat sink. A simple clamp, and two 6-32 (M3.5) screws can provide the minimum 125lb required mounting force.



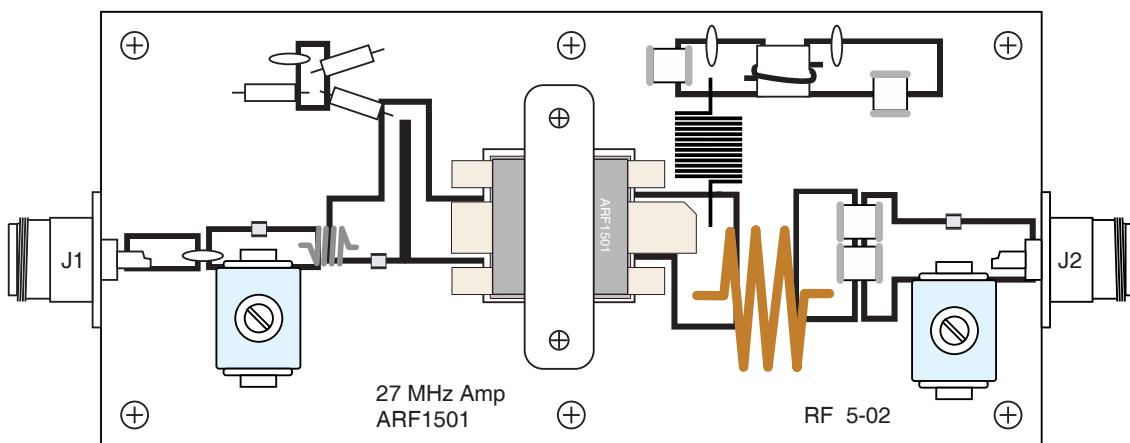
#### HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and mounting surface is beryllium oxide, BeO. Beryllium oxide dust is toxic when inhaled. Care must be taken during handling and mounting to avoid damage to this area. These devices must never be thrown away.

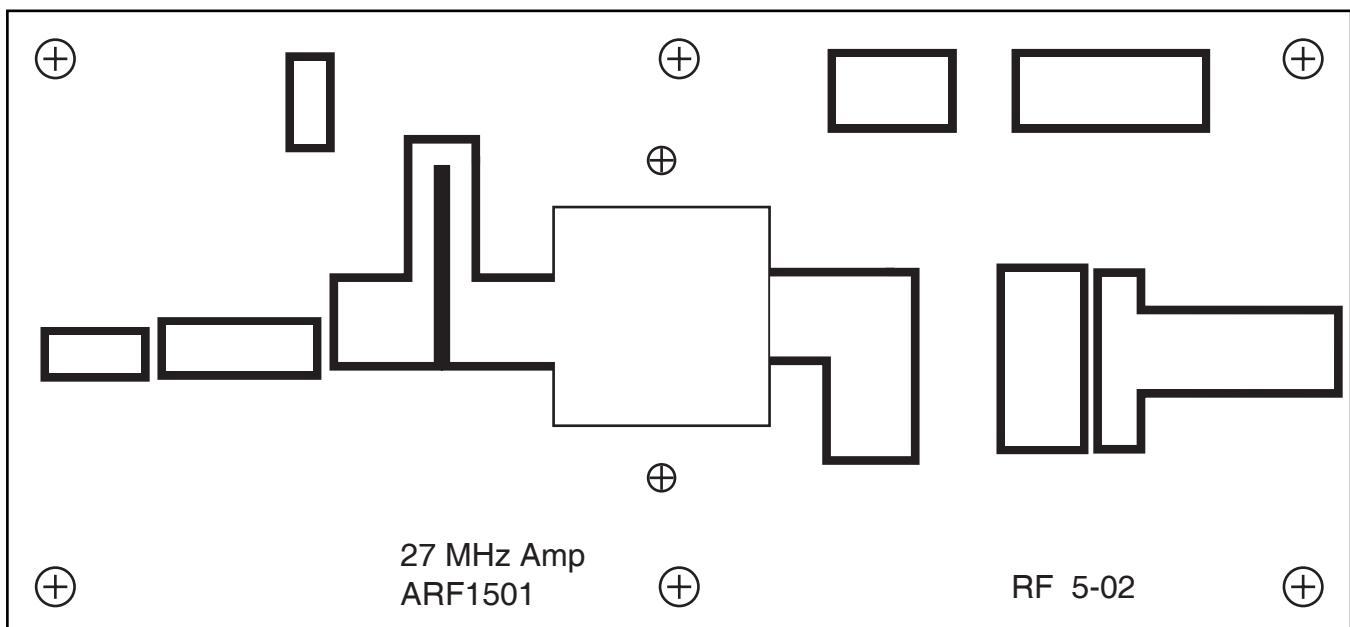
## ARF1501 -- 27.12 MHz Test Circuit



C1, C7,C8, C11 .1uF 250V ceramic chip  
 C2, C12 ARCO 465 75-380pF mica trimmer  
 C3 4700pF ATC700B  
 C4, C9-C11 8200pF 500V NPO ceramic  
 C5 - C6 150pF ATC 700B  
 L1 90 nH 4t #18 0.25" d .25" l  
 L2 175 nH - 3t #10 .75" dia .75" l  
 L3 2uH - 22t #24 enam. .312" dia.  
 L4 500nH 2t on 850u .5" bead  
 R1-R3 1k  $\Omega$  1/4W  
 TL1 .112" x 1.2" (50  $\Omega$ ) Stripline



Parts placement



1:1 pcb artwork